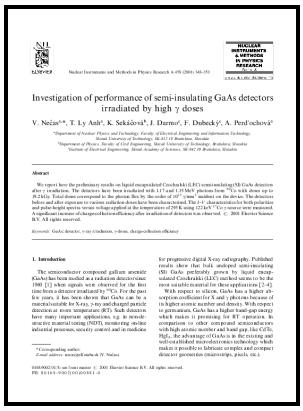
Semi-insulating GaAs

Academic Press - Method of manufacturing GaAs semiconductor device



Investigation of performance of semi-insulating GaAs detectors irradiated by high γ doses

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Gallium Arsenide (GaAs)

The dominant LN waveguide technology is characterized by a low refractive-index contrast which precludes the compact, large-angle bends and path-folding required for arrays; hence the highly elongated format e.

M05400

Semi-insulating GaAs is still GaAs. Other rules governing the width and span of air-bridges and minimum foot extension ripple through to a practical lower limit on the length of an electrode segment.

Microwaves101

The electrode metal film may be made of Al or a refractory metal silicide e.

semiconductor physics

Reflections at the RF discontinuities at either end create resonances within the tile. On one side of the substrate, a 1.

Potential of thick GaAs epitaxial layers for pixel detectors

Rib and deep-ridge waveguide sections are coupled by low-loss taper transitions which have been found to contribute no more than 0. Recently a researcher inquired about 150mm Gallium Arsenide with Chromium Cr doping. This paper gives an introduction into the concept of quantum imaging using direct conversion in segmented semiconductor arrays.

semiconductor physics

A method according to claim 1, wherein said etching stoppable AlGaAs layer has a thickness in the range from 1 to 10 nm.

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